XP132A0265SR

Power MOS FET

- ◆P-Channel Power MOS FET
- ◆DMOS Structure
- ◆Low On-State Resistance: 0.065Ω (max)
- ◆Ultra High-Speed Switching
- ◆SOP-8 Package

■General Description

The XP132A0265SR is a P-Channel Power MOS FET with low on-state resistance and ultra high-speed switching characteristics.
Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.
The small SOP-8 package makes high density mounting possible.

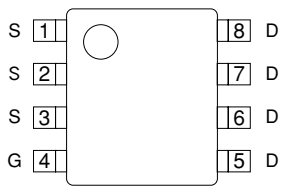
■Applications

- ●Notebook PCs
- ●Cellular and portable phones
- ●On-board power supplies
- ●Li-ion battery systems

■Features

Low on-state resistance : Rds(on)=0.065Ω(Vgs=-5V)
: Rds(on)=0.12Ω(Vgs=-2.5V)
Ultra high-speed switching
Operational Voltage : -2.5V
High density mounting : SOP-8

■Pin Configuration

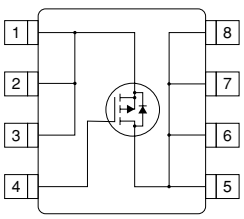


SOP-8
(TOP VIEW)

■Pin Assignment

PIN NUMBER	PIN NAME	FUNCTION
1 ～ 3	S	Source
4	G	Gate
5 ～ 8	D	Drain

■Equivalent Circuit



P-Channel MOS FET
(1 device built-in)

■Absolute Maximum Ratings

Ta=25℃

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	Vdss	-20	V
Gate-Source Voltage	Vgss	±12	V
Drain Current (DC)	Id	-6	A
Drain Current (Pulse)	Idp	-20	A
Reverse Drain Current	Idr	-6	A
Continuous Channel Power Dissipation (note)	Pd	2.5	W
Channel Temperature	Tch	150	℃
Storage Temperature	Tstg	-55~150	℃

Note: When implemented on a glass epoxy PCB

■Electrical Characteristics

DC Characteristics

Ta=25℃

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Drain Cut-off Current	Idss	Vds=-20V, Vgs=0V			-10	μA
Gate-Source Leakage Current	Igss	Vgs=±12V, Vds=0V			±10	μA
Gate-Source Cut-off Voltage	Vgs(off)	Id=-1mA, Vds=-10V	-0.5			V
Drain-Source On-state Resistance (note)	Rds(on)	Id=-3A, Vgs=-5V		0.055	0.065	Ω
		Id=-3A, Vgs=-2.5V		0.09	0.12	Ω
Forward Transfer Admittance (note)	|Yfs|	Id=-3A, Vds=-10V		8		S
Body Drain Diode Forward Voltage	Vf	If=-6A, Vgs=0V		-0.85	1.1	V

Note: Effective during pulse test.

Dynamic Characteristics

Ta=25℃

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Capacitance	Ciss	Vds=-10V, Vgs=0V f=1MHz		1100		pF
Output Capacitance	Coss			600		pF
Feedback Capacitance	Crss			220		pF

Switching Characteristics

Ta=25℃

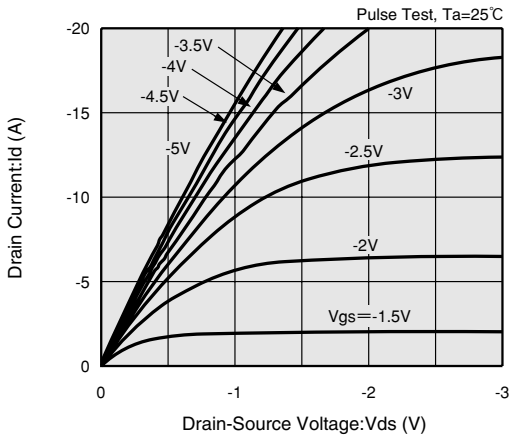
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Turn-on Delay Time	td (on)	Vgs=-5V, Id=-3A Vdd=-10V		15		ns
Rise Time	tr			15		ns
Turn-off Delay Time	td (off)			50		ns
Fall Time	tf			30		ns

Thermal Characteristics

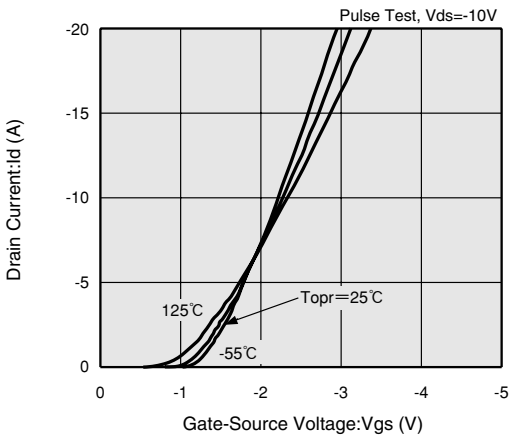
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Thermal Resistance (channel-ambience)	Rth (ch-a)	Implement on a glass epoxy resin PCB		50		˚C/W

■Typical Performance Characteristics

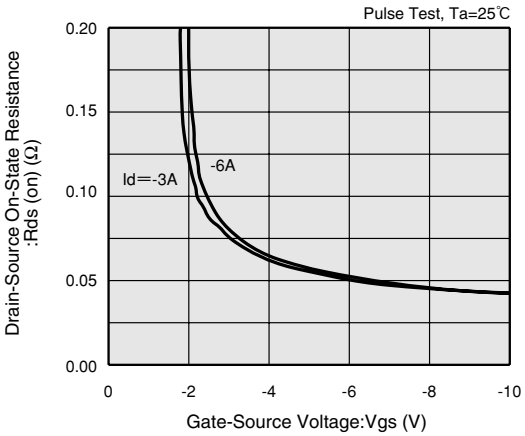
DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



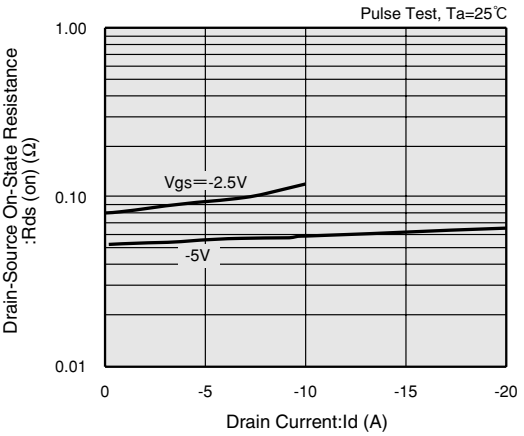
DRAIN CURRENT vs. GATE-SOURCE VOLTAGE



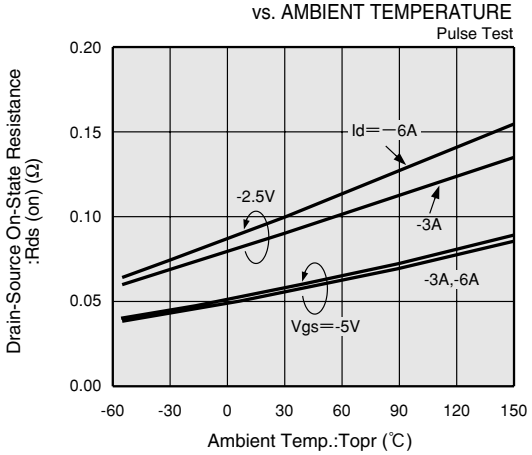
DRAIN-SOURCE ON-STATE RESISTANCE
vs. GATE-SOURCE VOLTAGE



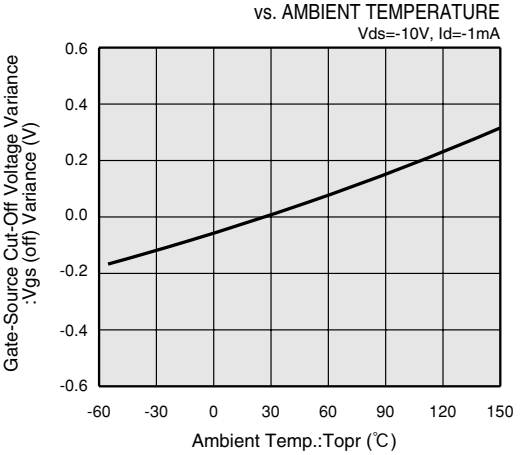
DRAIN-SOURCE ON-STATE RESISTANCE
vs. DRAIN CURRENT



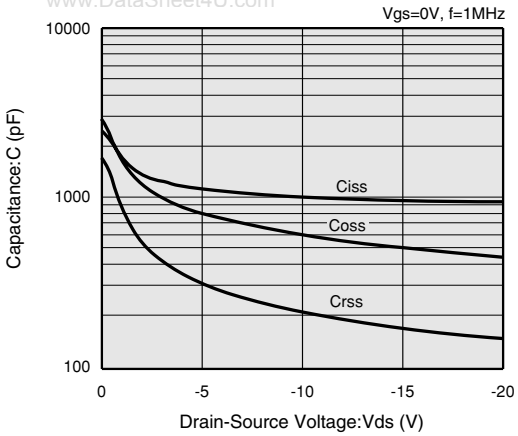
DRAIN-SOURCE ON-STATE RESISTANCE
vs. AMBIENT TEMPERATURE



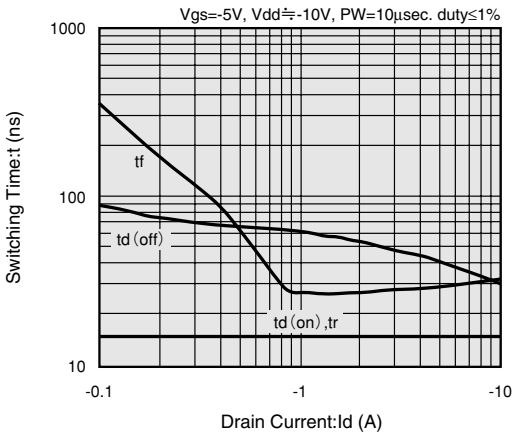
GATE-SOURCE CUT-OFF VOLTAGE VARIANCE
vs. AMBIENT TEMPERATURE



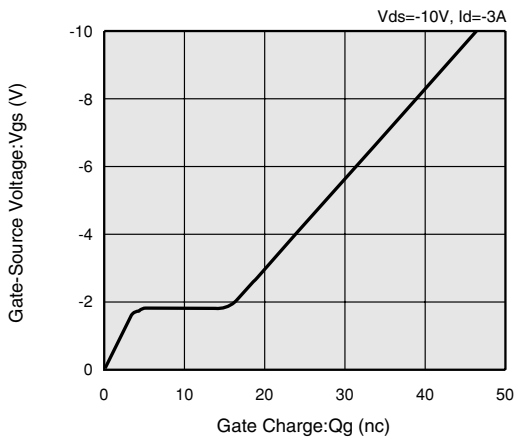
CAPACITANCE vs. DRAIN-SOURCE VOLTAGE



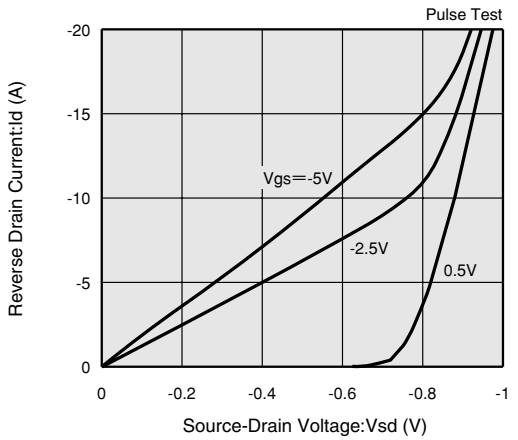
SWITCHING TIME vs. DRAIN CURRENT



GATE-SOURCE VOLTAGE vs. GATE CHARGE



REVERSE DRAIN CURRENT
vs. SOURCE-DRAIN VOLTAGE



STANDARDIZED TRANSITION THERMAL RESISTANCE vs. PULSE WIDTH